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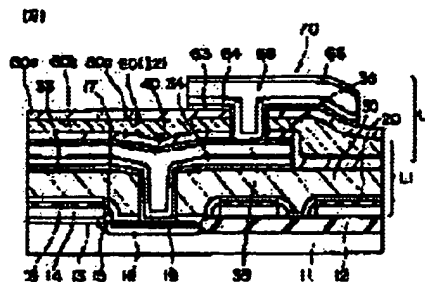
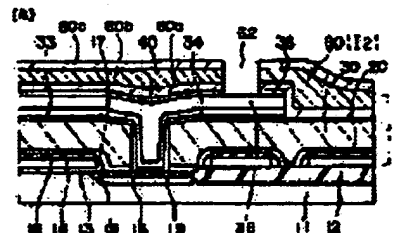
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## (54) SEMICONDUCTOR DEVICE AND MANUFACTURE THEREOF

## (57)Abstract:

**PROBLEM TO BE SOLVED:** To provide a semiconductor device without voids and breaking of wires and having superior step coverage using an aluminum alloy for the conductive material in a via hole, and to provide a manufacturing method of the semiconductor device.

**SOLUTION:** A via hole 62 is formed on a second interlayer insulating film 12 consisting of a silicon oxide film and formed on a substrate, at least on a layer of the wiring region located above the second layer, and by performed heat treatment at 300 to 550° C under a decompression state the gasified component contained in the interlayer insulating film is removed. A wetting layer 63 is formed on the surface of the interlayer insulating film 12 and the via hole 62, is cooled down to 100° C or lower, and the first aluminum film 64 is formed on the wetting layer 63 at a temperature of 200° C. The second aluminum film 65 is formed thereon at a temperature of 300° C or higher.



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